

**TC74VHC27F, TC74VHC27FN, TC74VHC27FS, TC74VHC27FT**

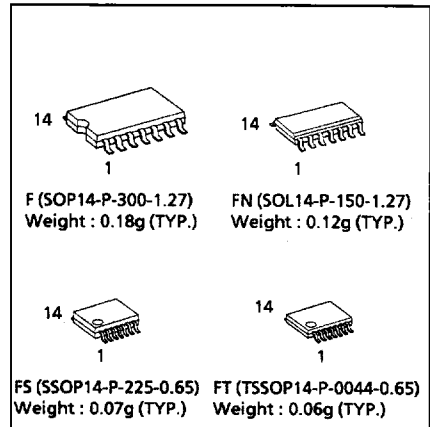
**TRIPLE 3-INPUT NOR GATE**

The TC74VHC27 is an advanced high speed CMOS 3-INPUT NOR GATE fabricated with silicon gate C<sup>2</sup>MOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

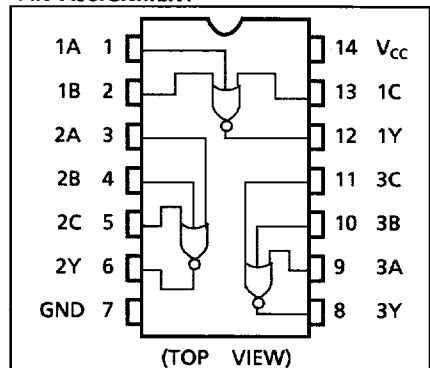
The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

**FEATURES :**

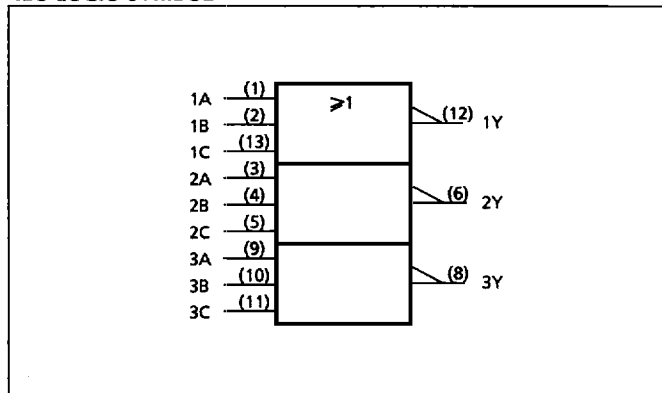
- High Speed..... $t_{pd} = 4.1ns$ (typ.) at  $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 2\mu A$ (Max.) at  $T_a = 25^{\circ}C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range..... $V_{CC} (opr) = 2V \sim 5.5V$
- Pin and Function Compatible with 74ALS27



**PIN ASSIGNMENT**



**IEC LOGIC SYMBOL**



**TRUTH TABLE**

A	B	C	Y
H	X	X	L
X	H	X	L
X	X	H	L
L	L	L	H

X : Don't Care

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**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5~7.0	V
DC Input Voltage	$V_{IN}$	-0.5~7.0	V
DC Output Voltage	$V_{OUT}$	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	-20	mA
Output Diode Current	$I_{OK}$	±20	mA
DC Output Current	$I_{OUT}$	±25	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	±50	mA
Power Dissipation	$P_D$	180	mW
Storage Temperature	$T_{stg}$	-65~150	°C

**RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	2.0~5.5	V
Input Voltage	$V_{IN}$	0~5.5	V
Output Voltage	$V_{OUT}$	0~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	dt/dv	0~100 ( $V_{CC} = 3.3 \pm 0.3V$ ) 0~20 ( $V_{CC} = 5 \pm 0.5V$ )	ns/V

**DC ELECTRICAL CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	$T_a = 25^\circ C$			$T_a = -40 \sim 85^\circ C$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	$V_{IH}$		2.0	1.50	—	—	1.50	—	V	
			3.0~5.5	$V_{CC} \times 0.7$	—	—	$V_{CC} \times 0.7$	—		
Low - Level Input Voltage	$V_{IL}$		2.0	—	—	0.50	—	0.50	V	
			3.0~5.5	—	—	$V_{CC} \times 0.3$	—	$V_{CC} \times 0.3$		
High - Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IL}$	$I_{OH} = -50 \mu A$	2.0	1.9	2.0	—	1.9	—	V
				3.0	2.9	3.0	—	2.9	—	
				4.5	4.4	4.5	—	4.4	—	
				3.0	2.58	—	—	2.48	—	
Low - Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 50 \mu A$	2.0	—	0.0	0.1	—	0.1	V
				3.0	—	0.0	0.1	—	0.1	
				4.5	—	0.0	0.1	—	0.1	
				3.0	—	—	0.36	—	0.44	
Input Leakage Current	$I_{IN}$	$V_{IN} = 5.5V \text{ or } GND$	0~5.5	—	—	±0.1	—	±1.0	$\mu A$	
			5.5	—	—	2.0	—	20.0		
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC} \text{ or } GND$	5.5	—	—	2.0	—	20.0	$\mu A$	

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**AC ELECTRICAL CHARACTERISTICS (Input  $t_r = t_f = 3ns$ )**

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT	
			V <sub>CC</sub> (V)	CL(pF)	MIN.	TYP.	MAX.		MIN.
Propagation Delay Time	t <sub>pLH</sub>	3.3 ± 0.3	15	—	6.2	8.8	1.0	10.5	ns
			50	—	8.7	12.3	1.0	14.0	
	5.0 ± 0.5	15	—	4.1	5.9	1.0	7.0		
		50	—	5.6	7.9	1.0	9.0		
Input Capacitance	C <sub>IN</sub>		—	4	10	—	10	pF	
Power Dissipation Capacitance	C <sub>PD</sub>	(Note 1)	—	20	—	—	—		

Note(1) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 3 \text{ (per Gate)}$$

**INPUT EQUIVALENT CIRCUIT**

